2SC4589

Silicon NPN Triple Diffused

HITACHI

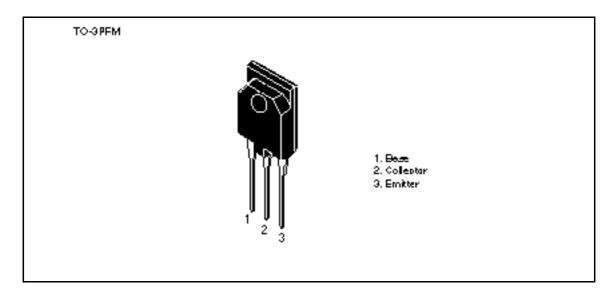
Application

CTV/character display horizontal deflection output

Features

- High speed switching $t_{\rm f}$ 0.5 μs
- High breakdown voltage $V_{CBO} = 1500 \text{ V}$
- Isolated package; TO-3PFM

Outline





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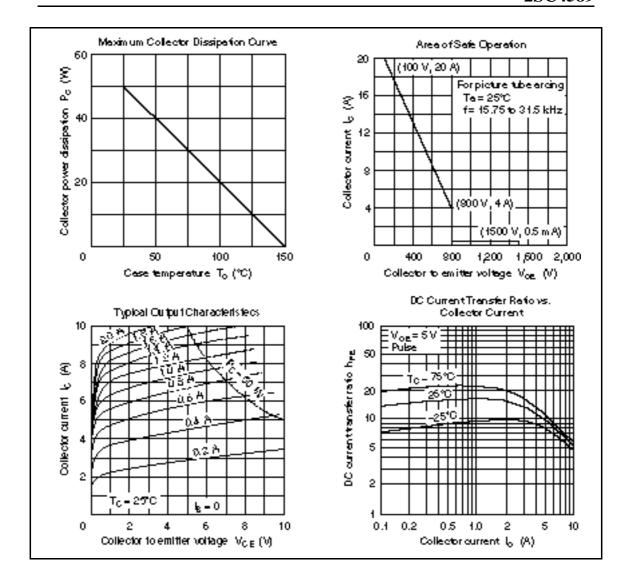
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit	
Collector to base voltage	V_{CBO}	1500	V	
Collector to emitter voltage	V_{CEO}	800	V	
Emitter to base voltage	V_{EBO}	5	V	
Collector current	I _c	10	Α	
Collector surge current	C (surge)	20	Α	
Collector power dissipation	P _c *1	50	W	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

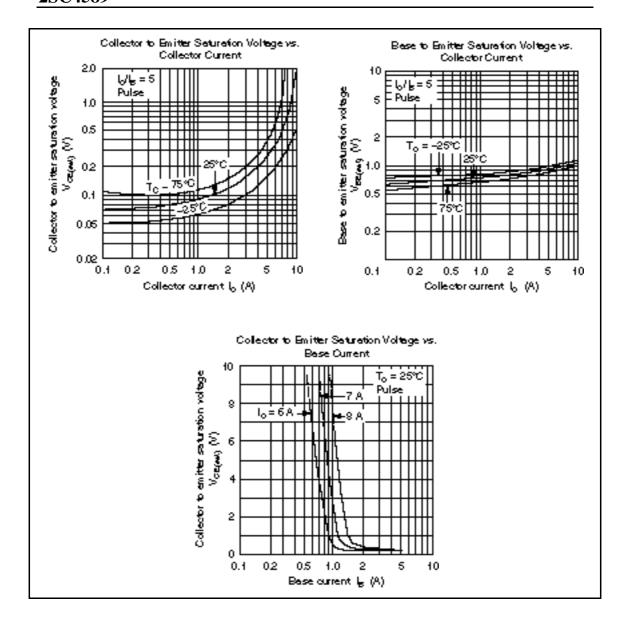
Note: 1. Value at $T_c = 25$ °C.

Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	800	_	_	V	$I_{\rm C}$ = 10 mA, $R_{\rm BE}$ =
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{\rm E} = 10 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I _{CES}		_	500	μΑ	$V_{CE} = 1500 \text{ V}, R_{BE} = 0$
DC current transfer ratio	h _{FE}	8	_	38		$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}$
Collector to emitter saturation voltage	V _{CE (sat)}	_	_	5	V	$I_{\rm C} = 8 \text{ A}, I_{\rm B} = 1.6 \text{ A}$
Base to emitter saturation voltage	$V_{BE\;(sat)}$	_	_	1.5	V	$I_{\rm C} = 8 \text{ A}, I_{\rm B} = 1.6 \text{ A}$
Fall time	t _f	_	0.2	0.5	μs	$I_{CP} = 7 \text{ A}, I_{B1} = 1.4 \text{ A}$



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